

ABSTRACT

A method for manufacturing buried connections in an integrated circuit, including the steps of: providing a structure formed of a first support wafer glued at the rear surface
5 of a thin semiconductor wafer, one or several elements of the integrated circuit being possibly formed in and above the thin wafer; gluing a second support wafer on the structure on the front surface side of the thin wafer; removing the first support wafer; forming connections between different areas of the rear surface of the thin wafer; gluing a third support wafer on the connections; and removing the second support wafer.